30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX T_A = +25°C
-30V	25mΩ @ V_{GS} = -10V	-6.8A
	38mΩ @ V_{GS} = -4.5V	-5.0A

Features

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/**
- **An automotive-compliant part is available under a separate datasheet (DMP3028LFDEQ)**

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

- DC-DC converters
- Power-management functions
- Load switches

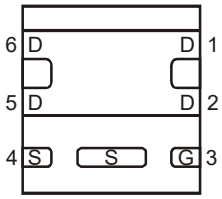
Mechanical Data

- Package: U-DFN2020-6
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0065 grams (Approximate)

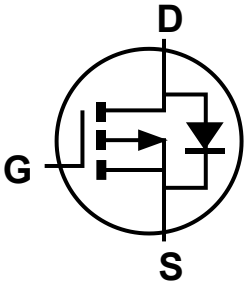
U-DFN2020-6 (Type E)



Bottom View



Pinout
Bottom View



Equivalent Circuit

Ordering Information (Note 4)

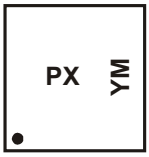
Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMP3028LFDE-7	U-DFN2020-6 (Type E)	3,000	Tape & Reel
DMP3028LFDE-13	U-DFN2020-6 (Type E)	10,000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

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Marking Information

Site 1



PX = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: M = 2025)
M = Month (ex: 9 = September)

Date Code Key

Year	2012	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	Z	-	M	N	P	R	S	T	U	V	W	X

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



PX = Product Type Marking Code
YWX = Date Code Marking
Y = Year (ex: 5 = 2025)
W = Week (ex: a = Week 27; z Represents Week 52 and 53)
X = Internal Code (ex: U = Monday)

Date Code Key

Year	2012	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	2	-	5	6	7	8	9	0	1	2	3	4

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-6.8 -5.3	A
	t < 10s	T_A = +25°C T_A = +70°C	I_D	-8.2 -6.6	A
Maximum Body Diode Forward Current (Note 5)			I_S	-2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-40	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	0.66	W
	T_A = +70°C		0.42	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	189	°C/W
	t < 10s		125	
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	2.03	W
	T_A = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	61	°C/W
	t < 10s		41	
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	9.3	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -30V, V_{GS} = 0
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.2	—	-2.4	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	20	25	mΩ	V_{GS} = -10V, I_D = -7A
		—	29	38		V_{GS} = -4.5V, I_D = -6.2A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	4.5	—	s	V_{DS} = -5V, I_D = -7A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0, I_S = -2.1A
On-State Drain Current (Note 8)	$I_{D(ON)}$	-20	—	—	A	V_{DS} ≦ -5V, V_{GS} = -4.5V
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1241	1860	pF	V_{DS} = -15V, V_{GS} = 0 f = 1.0MHz
Output Capacitance	C_{oss}	—	147	220		
Reverse Transfer Capacitance	C_{rss}	—	110	165		
Gate Resistance	R_G	—	15	30	Ω	V_{DS} = 0, V_{GS} = 0, f = 1.0MHz
Total Gate Charge (V_{GS} = -10V)	Q_g	—	22	33	nC	V_{DS} = -15V, I_D = -7A
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	10.9	17		
Gate-Source Charge	Q_{gs}	—	3.5	6		
Gate-Drain Charge	Q_{gd}	—	4.7	8		
Turn-On Delay Time	$t_{D(on)}$	—	9.7	15	ns	V_{GS} = -10V, V_{DD} = -15V R_{GEN} = 6Ω, I_D = -7A
Turn-On Rise Time	t_r	—	17.1	26		
Turn-Off Delay Time	$t_{D(off)}$	—	60.5	91		
Turn-Off Fall Time	t_f	—	40.4	61		

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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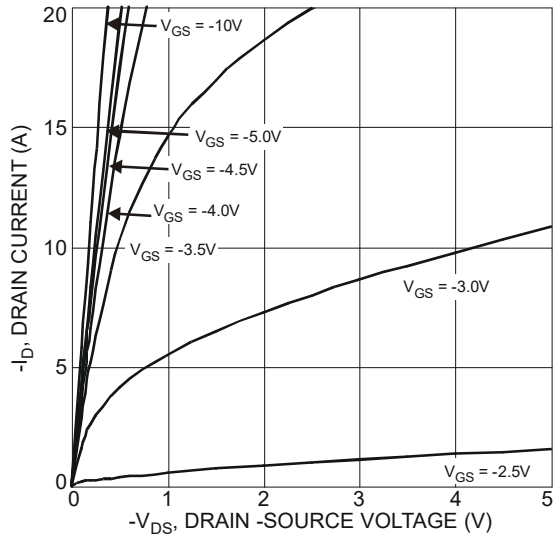


Figure 1 Typical Output Characteristics

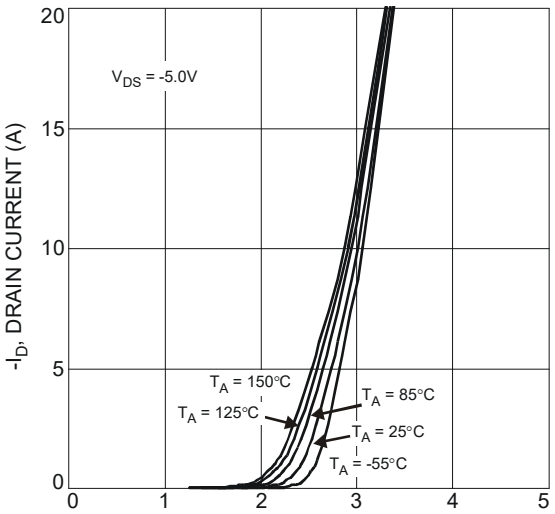


Figure 2 Typical Transfer Characteristics

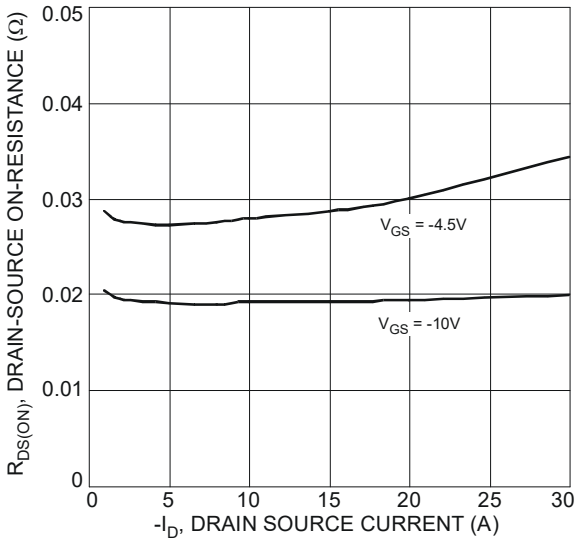


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

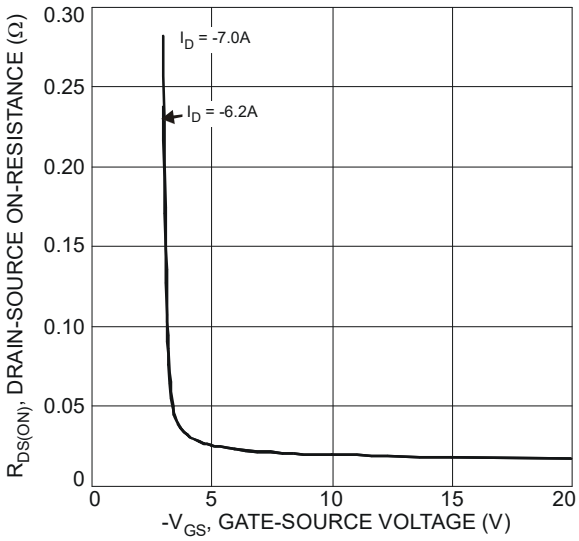


Figure 4 Typical Drain-Source On-Resistance
vs. Gate-Source Voltage

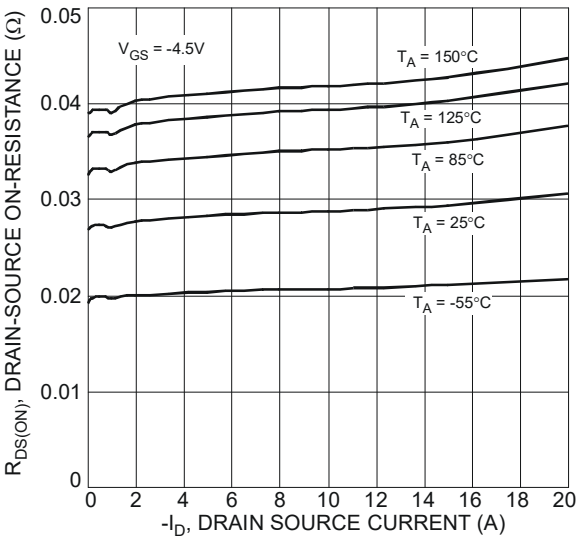


Figure 5 Typical On-Resistance vs.
Drain Current and Temperature

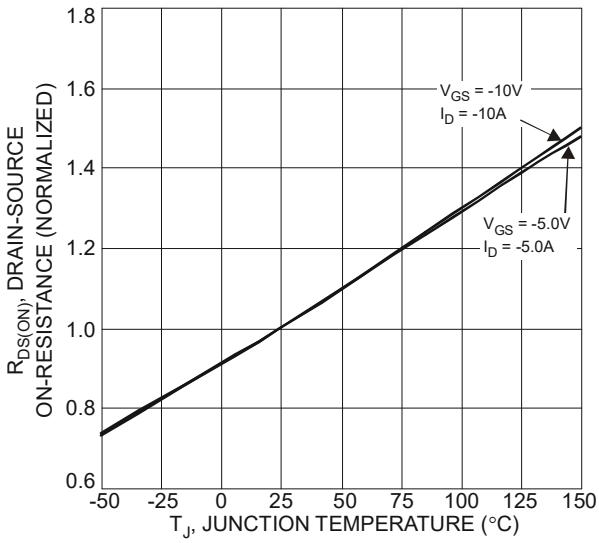


Figure 6 On-Resistance Variation with Temperature

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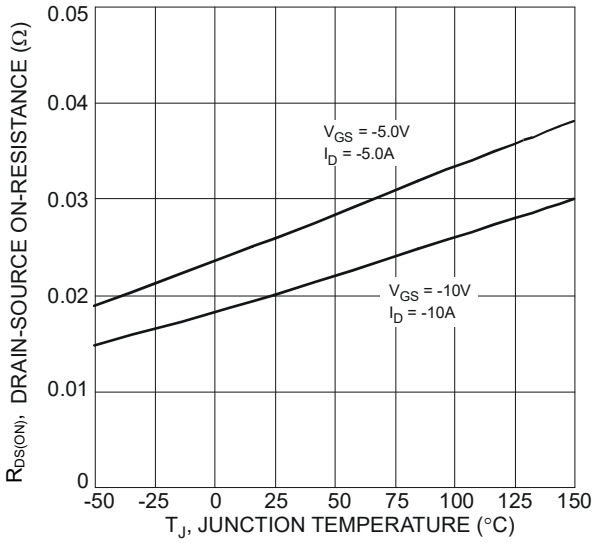


Figure 7 On-Resistance Variation with Temperature

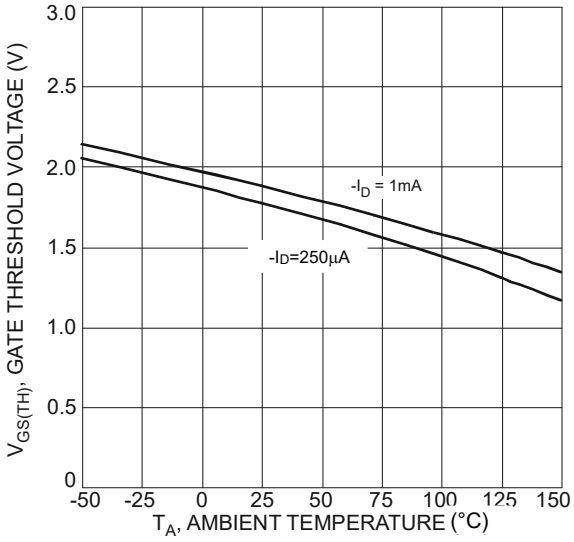


Figure 8 Gate Threshold Variation vs. Ambient Temperature

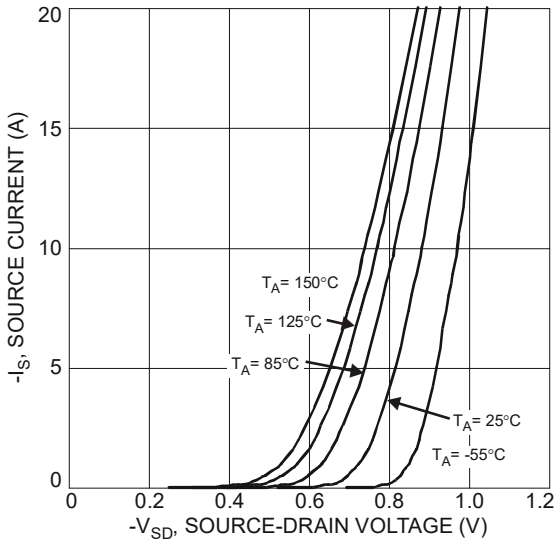


Figure 9 Diode Forward Voltage vs. Current

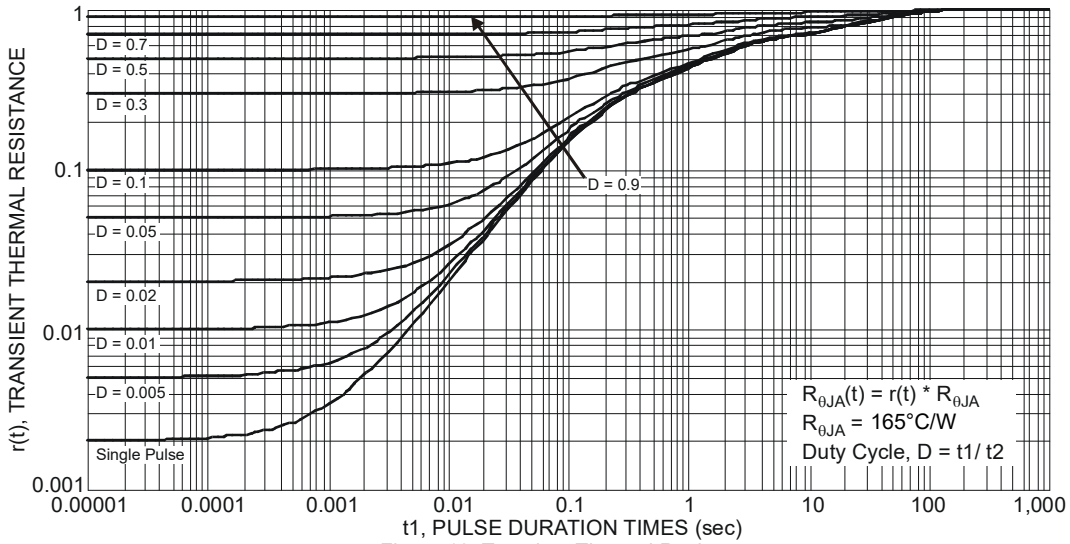


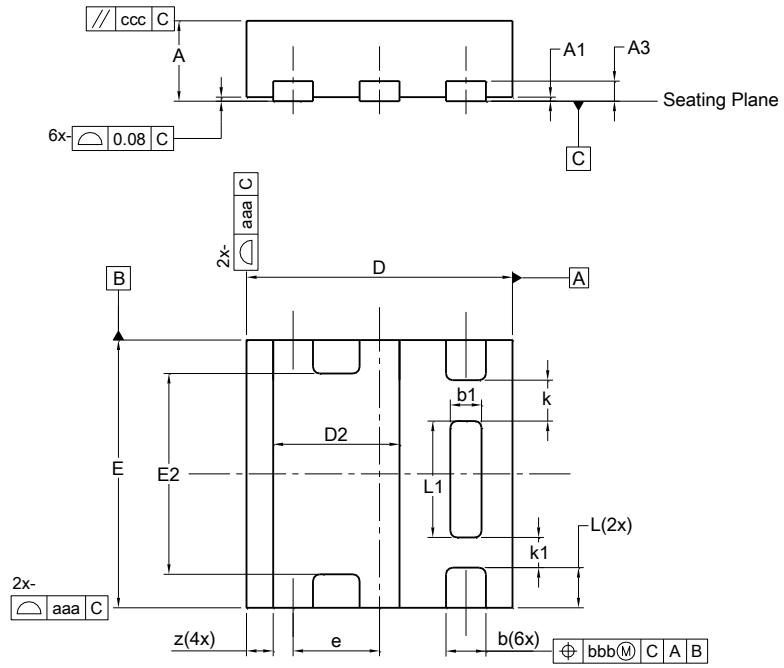
Figure 10 Transient Thermal Resistance

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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)

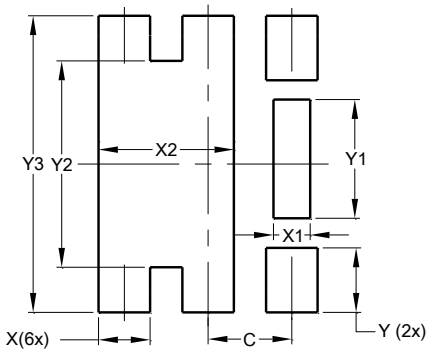


U-DFN2020-6 (Type E)			
Dim	**Min**	**Max**	**Typ**
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	–	–	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	–	–	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
k	–	–	0.305
k1	–	–	0.225
Z	–	–	0.20
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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